

## METHOD OF EXTENDING THE AREAS OF CLEAR FIELD PHASE SHIFT GENERATION

### ABSTRACT OF THE DISCLOSURE

An exemplary Full Phase patterning method involves patterning gates to increase process margins from conventional methods. This technique can define all poly patterns with a phase mask, using only a field or trim mask to resolve conflicts in the phase mask. The trim mask exposes a series of lines that either separates the different phase areas where patterns are not desired or minimizes the range of sizes of the phase patterns next to a critical gate area.

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